
MR27V3255D

1,048,576-Double Word x 32-Bit or 2,097,152-Word x 16-Bit

8-Double Word x 32-Bit or 16-Word x 16-Bit Page Mode

Production Programmed Read Only Memory (P2ROM)

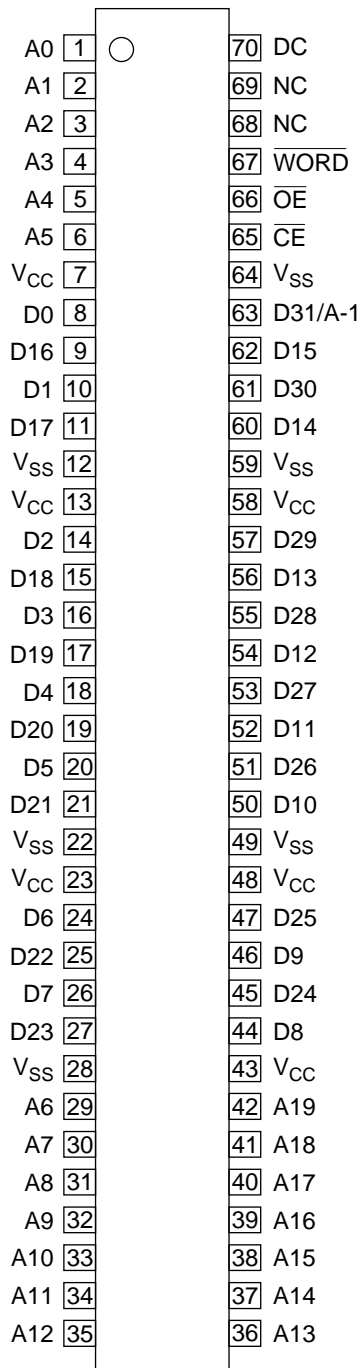
DESCRIPTION

The MR27V3255D is a 32Mbit Production Programmed Read-Only Memory (P2ROM) with page mode. Its configuration can be electrically switched between 1,048,576 double word x 32bit and 2,097,152 word x 16bit. The MR27V3255D operates on a single +3.3V power supply and is TTL compatible. The MR27V3255D provides Page mode which can greatly reduce the read access time. Since the MR27V3255D operates asynchronously, external clocks are not required, making this device easy-to-use. The MR27V3255D is suitable as large-capacity fixed memory for microcomputers and data terminals. It is manufactured using a CMOS double silicon gate technology and is offered in 70-pin SSOP or 70-pin TSOP packages.

FEATURES

- 1,048,576 double word x 32bit / 2,097,152 word x 16bit electrically switchable configuration
- Single +3.3V power supply
- Access time 70ns
 - Page mode access time 25ns
- Input / Output TTL compatible
- Three-state output
- Packages
 - 70-pin plastic SSOP (SSOP70-P-500-0.80-K) (Product name : MR27V3255D-xxMB)
 - 70-pin plastic TSOP (TSOP II 70-P-400-0.65-K) (Product name : MR27V3255D-xxTA)

PIN CONFIGURATION (TOP VIEW)

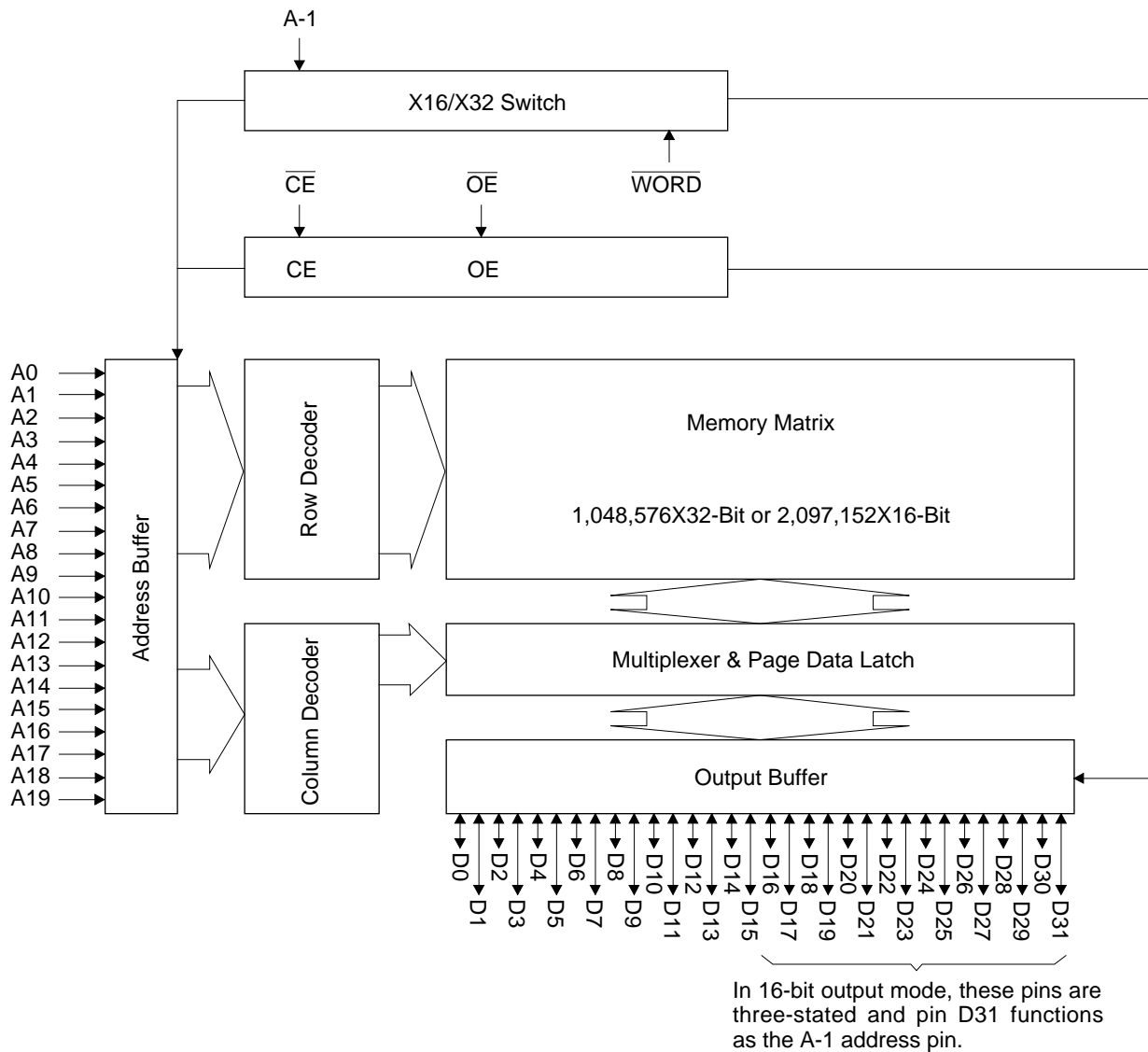


70-pin SSOP , TSOP (II)

PIN NAMES	FUNCTIONS
D31/A-1	Data output / Address input
A0 - A19	Address input
D0 - D30	Data output
\overline{CE}	Chip enable
\overline{OE}	Output enable
V_{CC}	Power supply voltage
V_{SS}	GND
\overline{WORD}	Mode switch
DC	Don't care *
NC	Non connection

* : Logical input level is ignored , however the pin is connected to internal circuit.

BLOCK DIAGRAM



FUNCTION TABLE

MODE	CE	OE	WORD	DC	V _{CC}	D0 - D15	D16 - D30	D31/A-1
READ (32-Bit)	L	L	H	**	3.3V	D _{OUT}		
READ (16-Bit)	L	L	L			D _{OUT}	Hi-Z	L/H
OUTPUT DISABLE	L	H	H			Hi-Z		*
			L			Hi-Z		*
STAND-BY	H	*	H	Hi-Z		*		
			L	Hi-Z		*		

* : Don't Care (H or L)

** : Don't Care (H or L or Open)

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Value	Unit
Operating temperature under bias	T_{opr}	-	0 to 70	°C
Storage temperature	T_{stg}		-55 to 125	°C
Input voltage	V_I	relative to V_{SS}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_O		-0.5 to $V_{CC} + 0.5$	V
Power supply voltage	V_{CC}		-0.5 to 5	V
Power dissipation per package	P_D	-	1.0	W

RECOMMENDED OPERATING CONDITIONS FOR READ

(Ta=0 to 70°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
V_{CC} power supply voltage	V_{CC}	$V_{CC}=3.0V-3.6V$	3.0	-	3.6	V
Input "H" level	V_{IH}		2.2	-	$V_{CC}+0.5^*$	V
Input "L" level	V_{IL}		-0.5**	-	0.6	V

Voltage is relative to V_{SS} * : $V_{CC}+1.5V$ (Max.) when pulse width of overshoot is less than 10nS.

** : -1.5V (Min.) when pulse width of undershoot is less than 10nS.

ELECTRICAL CHARACTERISTICS (Read operation)**DC Characteristics** $(V_{CC}=3.3V\pm 0.3V, T_a=0 \text{ to } 70^\circ\text{C})$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input leakage current	I_{LI}	$V_I=0 \text{ to } V_{CC}$	-	-	10	μA
Output leakage current	I_{LO}	$V_O=0 \text{ to } V_{CC}$	-	-	10	μA
V_{CC} power supply current (Standby)	I_{CS1}	$\overline{CE}=V_{CC}$	-	-	50	μA
	I_{CS2}	$\overline{CE}=V_{IH}$	-	-	1	mA
V_{CC} power supply current (Read)	I_{CCA}	$\overline{CE}=V_{IL}, \overline{OE}=V_{IH}$ $t_c=70\text{ns}$	-	-	100	mA
Input "H" level	V_{IH}	-	2.2	-	$V_{CC}+0.5^*$	V
Input "L" level	V_{IL}	-	-0.5**	-	0.6	V
Output "H" level	V_{OH}	$I_{OH}=-400\mu\text{A}$	2.4	-	-	V
Output "L" level	V_{OL}	$I_{OL}=2.1\text{mA}$	-	-	0.4	V

Voltage is relative to V_{SS} * : $V_{CC}+1.5\text{V}$ (Max.) when pulse width of overshoot is less than 10nS.

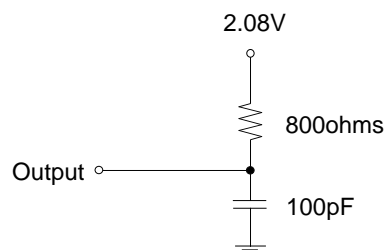
** : -1.5V (Min.) when pulse width of undershoot is less than 10nS.

AC Characteristics $(V_{CC}=3.3V\pm 0.3V, T_a=0 \text{ to } 70^\circ\text{C})$

Parameter	Symbol	Condition	Min.	Max.	Unit
Address access cycle time	T_C	-	70	-	ns
Address access time	T_{ACC}	$\overline{CE}=\overline{OE}=V_{IL}$	-	70	ns
Page access cycle time	T_{PC}	-	25	-	ns
Page access time	T_{PAC}	-	-	25	ns
\overline{CE} access time	T_{CE}	$\overline{OE}=V_{IL}$	-	70	ns
\overline{OE} access time	T_{OE}	$\overline{CE}=V_{IL}$	-	25	ns
Output disable time	T_{CHZ}	$\overline{OE}=V_{IL}$	0	25	ns
	T_{OHZ}	$\overline{CE}=V_{IL}$	0	20	ns
Output hold time	T_{OH}	$\overline{CE}=\overline{OE}=V_{IL}$	0	-	ns

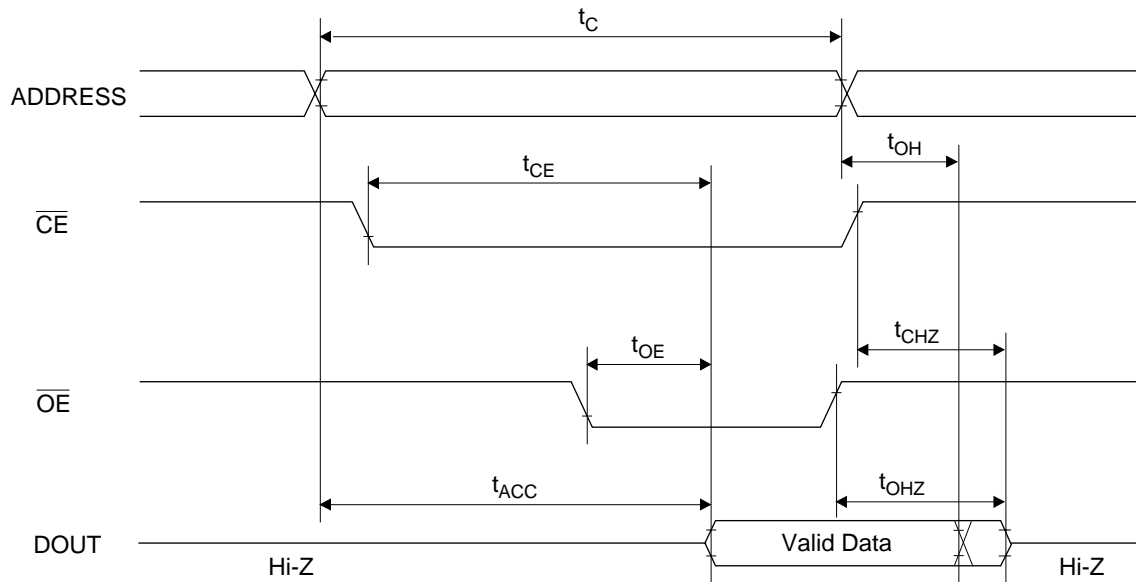
Measurement conditions

Input signal level	-----	0V/3V
Input timing reference level	-----	0.8V/2.0V
Output load	-----	100pF
Output timing reference level	-----	0.8V/2.0V

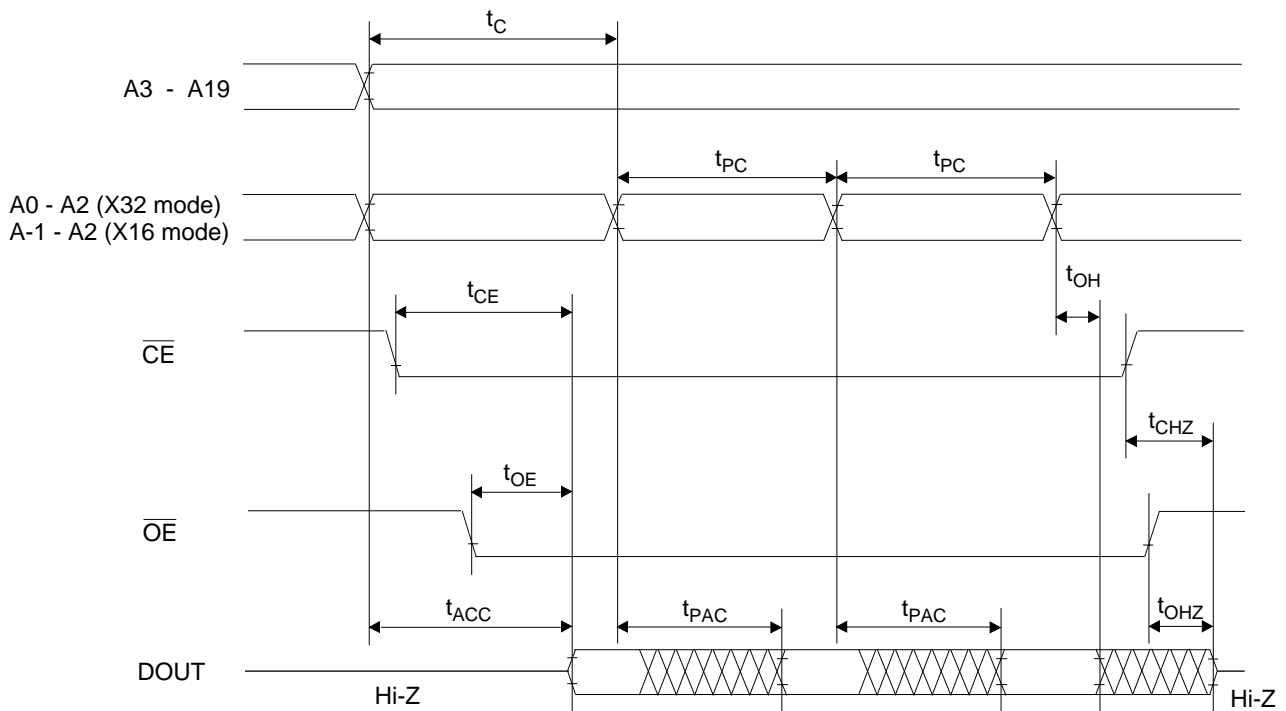


TIMING CHART

NORMAL MODE READ CYCLE



PAGE MODE READ CYCLE



PIN Capacitance $(V_{CC}=3.3V, T_a=25^{\circ}C, f=1MHz)$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input	C_{IN}	$V_I=0V$	-	-	8	pF
Output	C_{OUT}	$V_O=0V$	-	-	10	